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PARAMETER	SYMBOL	TYP		MAX.			UNIT	
Maximum Junction-to-Ambient	R _{thJA}	-		40				
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.24		-			°C/W	
Maximum Junction-to-Case (Drain)	R _{thJC}	-		0.34				
SPECIFICATIONS ($T_J = 25 \text{ °C}$, u	nless otherw	ise noted)				1		r
PARAMETER	SYMBOL	TES	T CONDITIO	NS	MIN.	TYP.	MAX.	UNI
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250) μΑ	500	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	e to 25 °C, I _D :	= 1 mA ^d	-	0.27	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250	Ο μΑ	3.0	-	5.0	V
Gate-Source Leakage	I _{GSS}		$V_{GS} = \pm 30 V$		-	-	± 100	nA
Zara Cata Valtaga Drain Current	le e e	V _{DS} =	= 500 V, V _{GS} =	= 0 V	-	-	50	μA
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 400 \	/, V _{GS} = 0 V, T	_J = 125 °C	-	-	2.0	mA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D =	14 A ^b	-	0.190	0.235	Ω
Forward Transconductance	g _{fs}	V _{DS}	= 50 V, I _D = 14	4 A ^b	12	-	-	S
Dynamic								
Input Capacitance	C _{iss}		$V_{GS} = 0 V,$		-	3600	-	
Output Capacitance	C _{oss}		$V_{DS} = 25 V$,		-	380	-	
Reverse Transfer Capacitance	C _{rss}	f = 1	.0 MHz, see fi	g. 5	-	37	-	
	0		V _{DS} = 1.0 V	, f = 1.0 MHz	-	4800	-	рF
Output Capacitance	Coss		V _{DS} = 400 V	' , f = 1.0 MHz	-	100	-	р.
Effective Output Capacitance	Coss eff.	$V_{GS} = 0 V$	$V_{DS} = 0 V$	' to 400 V ^c	-	220	-	
Effective Output Capacitance (Energy Related)	C _{oss} eff. (ER)		V _{DS} = 0 V	to 400 V ^d	-	160	-	
Internal Gate Resistance	R _G	f = 1	MHz, open d	rain	-	1.2	-	Ω
Total Gate Charge	Qg		L = 22 A	V _{DS} = 400 V	-	-	150	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V		50	-	-	44	nC
Gate-Drain Charge	Q _{gd}		see fig.	6 and 13 ^b	-	-	72	
Turn-On Delay Time	t _{d(on)}	Voo	= 250 V, I _D = 2	23 A	-	26	-	
Rise Time	t _r				-	94	-	1
Turn-Off Delay Time	t _{d(off)}	R _g :	= 6.0, V _{GS} = 1	UV	-	53	-	ns
Fall Time	t _f	1	see fig. 10 ^b		-	45	-	1
Drain-Source Body Diode Characteristic	s	·						
Continuous Source-Drain Diode Current	I _S	MOSFET sym showing the	bol		_	-	23	_
Pulsed Diode Forward Current ^a	I _{SM}	integral revers			-	-	92	A
Body Diode Voltage	V _{SD}	T _{.J} = 25 °C	C, I _S = 14 A, V	_{GS} = 0 V ^b	-	-	1.5	V
		T _J = 25 °C			-	170	250	
Body Diode Reverse Recovery Time	t _{rr}	T _J = 125 °C	 c –	23 A,	-	220	330	ns
		$T_J = 25 \text{ °C}$		20 <u>Λ,</u> 100 Α/μs ^b	-	560	840	
Body Diode Reverse Recovery Charge	Q _{rr}	T _J =1 25 °C		-	-	980	1500	μC
Reverse Recovery Current	I _{RRM}		T _J = 25 °C		-	7.6	11	A
Forward Turn-On Time	t _{on}	Intrinsic tu		negligible (turn-	on is dor	1		

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width $\leq 300 \ \mu$ s; duty cycle $\leq 2 \ \%$. c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising fom 0 % to 80 % V_{DS} . d. C_{oss} eff. (ER) is a fixed capacitance that stores the same energy time as C_{oss} while V_{DS} is rising fom 0 % to 80 % V_{DS} .

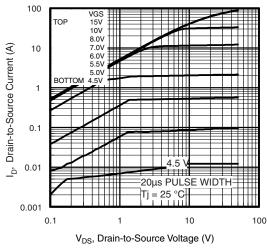
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

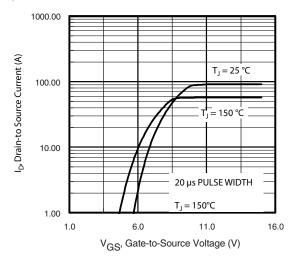


Fig. 3 - Typical Transfer Characteristics

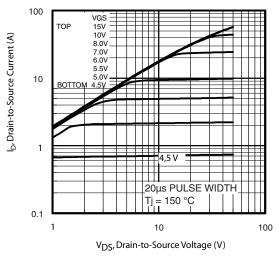


Fig. 2 - Typical Output Characteristics

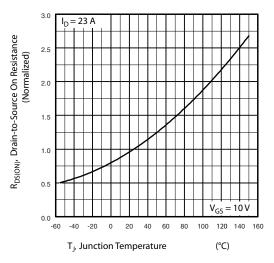


Fig. 4 - Normalized On-Resistance vs. Temperature

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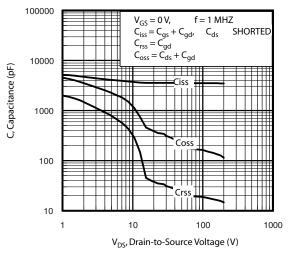


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

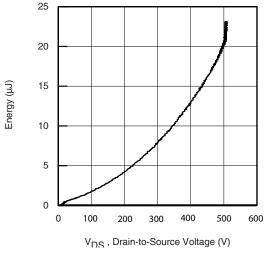


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

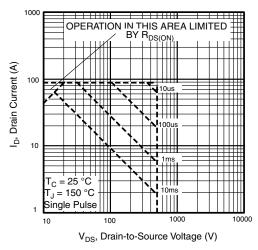


Fig. 7 - Maximum Safe Operating Area

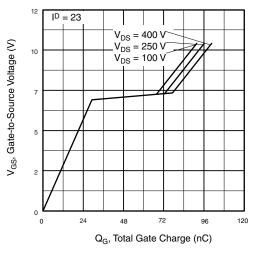


Fig. 8 - Typical Gate Charge vs. Gate-to-Source Voltage

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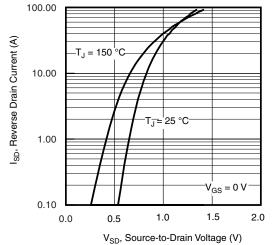


Fig. 9 - Typical Source-Drain Diode Forward Voltage

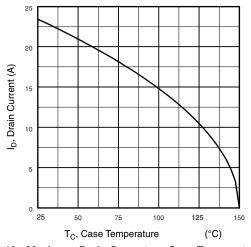


Fig. 10 - Maximum Drain Current vs. Case Temperature

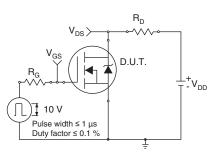


Fig. 11a - Switching Time Test Circuit

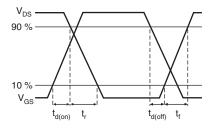


Fig. 11b - Switching Time Waveforms

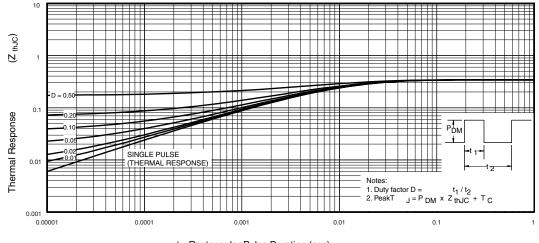




Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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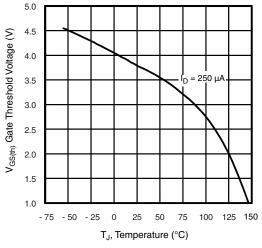


Fig. 13 - Threshold Voltage vs. Temperature

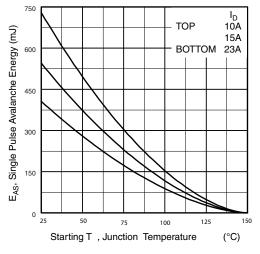


Fig. 14 - Maximum Avalanche Energy s. Drain Current

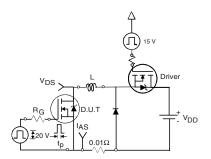


Fig. 15a - Unclamped Inductive Test Circuit

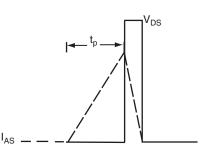


Fig. 15b - Unclamped Inductive Waveforms

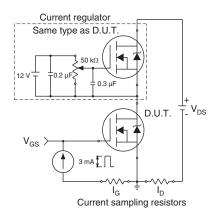


Fig. 16a - Gate Charge Test Circuit

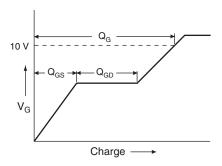


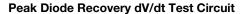
Fig. 16b - Basic Gate Charge Waveform

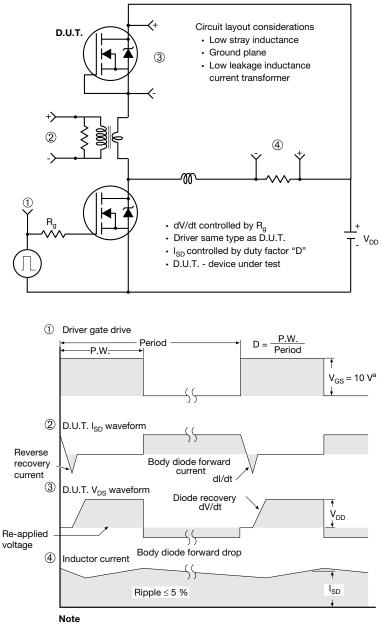
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a. V_{GS} = 5 V for logic level devices

Fig. 17 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

1	 \

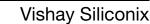
	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØР	3.56	3.65	7
Ø P1	7.19) ref.	
Q	5.31	5.69	
S	5.54	5.74	

Notes

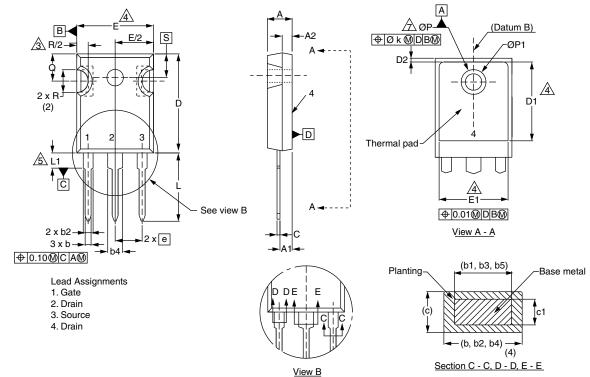
- ⁽¹⁾ Package reference: JEDEC[®] TO247, variation AC
- (2) All dimensions are in mm
- ⁽³⁾ Slot required, notch may be rounded
- ⁽⁴⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁵⁾ Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

Revision: 19-Oct-2020





VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
с	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

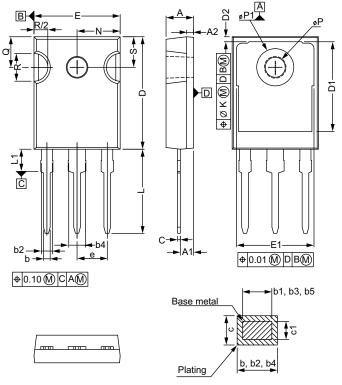
Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- ⁽²⁾ Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- ⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c



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VERSION 3: FACILITY CODE = N



	MILLIMETERS			MILLIMETERS	
DIM.	MIN.	MAX.	DIM.	MIN.	MAX.
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	e	5.46	BSC
b1	0.99	1.35	k	0.2	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62 BSC	
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51 BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

⁽³⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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